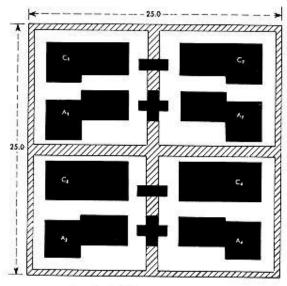
DIONICS INC.

RUSHMORE ST., WESTBURY, N.Y. 11590 516+997+747



DI 914 Dielectrically Isolated DIODE QUAD

WITH CLOSELY MATCHED FORWARD CHARACTERISTICS 100% PROBED



Dimensions in Mils

Dielectric Isolation

Aluminum

- Chip Thickness=6 Mils ±1 Mil
- Min. Dimension Across Bonding Pads=4.0 Mils
 Min. Separation Between Bonding Pads=1.75 Mils
- Distance from Bonding Pads to Edge of Chips -- 1.75 Mils

Detailed Specifications on Reverse Side

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DI 914 Dielectrically Isolated DIODE QUAD

WITH CLOSELY MATCHED FORWARD CHARACTERISTICS 100% PROBED

- Dielectric Isolation Monolithic Construction Superior Thermal Tracking
- Close Parameter Match Available in Chip or TO 5 Package

For use in hybrid circuits. Can be wired into bridge configurations: (a) in parallel, for higher current diode and rectifier applications; (b) in series strings; or (c) as 4 densely-packed individual diodes. Matched characteristics are uniform over the current range 100µA to 100mA.

Among the features are: Dielectric Isolation; monolithic construction; close parameter match:

Among the features are: Dielectric Isolation; monolithic construction; close parameter match; and superior thermal tracking. The use of this versatile chip provides a savings in space, as well as reduced die-bonding time at harmful elevated temperatures.

The 4 diodes are Dielectrically Isolated from each other and from the bottom of the chip, with more than 1,000 volts isolation between

individual diodes.

The chips are gold-backed, permitting conventional eutectic die-bonding techniques. Aluminum metallizing on bonding pads permits utilization of conventional wire-bonding techniques. Since the bottom of the DI chip is not used for electrical contact, it is possible to die-bond with pure epoxy or adhesive films. Excellent mechanical and thermal properties are thus easily achieved, without the substrate or its components being subjected to high temperatures. Chips are shipped in 2" x 2" plastic compartmented containers, 400 chips in each container, with each chip in its own compartment. Probed slices are individually packed in plastic carriers.

	Maiched Characteristic ΔVr mVMax. @ Ir =1.0mA	V ₈₁ Voite Min. @I ₂ —100 _β A	i _k μA Max, @ V _a Voits	l, mA Min. @ V,=1.0V	C _f pf Max.	t,, Max. @ I _f =10mA; recover to i _m =1 mA
DI 914-1QM -2QM -3QM	2.0	75 60 45	.010 @ 65 .010 @ 50 .010 @ 35	20	3.0	100 nsec. *
DI 914-1Q -2Q -3Q	30.0	75 60 45	.025 @ 65 .025 @ 50 .025 @ 35	10	3.0	100 nsec. 1

^{*}Also available with t_{rr} Max. @ 4 nsec.